

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

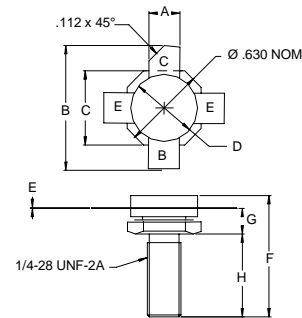
The **ASI BLX14** is Designed for HF and VHF band applications.

**FEATURES:**

- $P_G = 13$  dB min. at 15 W/1.6 MHz
- $d_3 = -40$  dB typ. at 15 W(PEP)
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	4.0 A
$V_{CBO}$	85 V
$V_{EBO}$	4.0 V
$V_{CEO}$	36 V
$P_{DISS}$	88 W @ $T_C = 25$ °C
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +200 °C
$\theta_{JC}$	1.99 °C/W

**PACKAGE STYLE .500 4L STUD (A)**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B		1.050 / 26.67
C	.545 / 13.84	.555 / 14.10
D	.495 / 12.57	.505 / 12.83
E	.003 / 0.08	.007 / 0.18
F		.830 / 21.08
G	.185 / 4.70	.198 / 5.03
H	.497 / 12.62	.530 / 13.46

**CHARACTERISTICS**  $T_C = 25$  °C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 25$ mA		85			V
$BV_{CER}$	$I_C = 25$ mA	$R_{BE} = 5.0$ Ω	85			V
$BV_{CEO}$	$I_C = 50$ mA		36			V
$BV_{EBO}$	$I_E = 10$ mA		4.0			V
$h_{FE}$	$V_{CE} = 6.0$ V	$I_C = 1.4$ A	15		100	---
$f_T$	$V_{CE} = 20$ V	$I_C = 3.0$ A		250		MHz
$C_C$	$V_{CB} = 30$ V	$f = 1.0$ MHz		115	125	pF
$G_P$ $d_3$	$V_{CE} = 28$ V $f = 1.6$ MHz	$I_{CQ} = 2.0$ A $P_{OUT} = 15$ W(PEP)	13	-40		dB dB